



COMSET
SEMICONDUCTORS

NPN BDX33 – BDX33A – BDX33B – BDX33C

PNP BDX34 – BDX34A – BDX34B – BDX34C

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

The BDX33B, BDX33B and BDX33C are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package.

They are intended for use in power linear and switching applications.

The complementary PNP types are the BDX34A, BDX34B and BDX34C respectively.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage	BDX33	45	V
		BDX34		
		BDX33A	60	
		BDX34A		
		BDX33B	80	
		BDX34B		
V_{CEV}	Collector-Emitter Voltage	BDX33C	100	V
		BDX34C		
		BDX33	45	
		BDX34		
		BDX33A	60	
		BDX34A		
	$I_B=0$	BDX33B	80	
		BDX34B		
		BDX33C	100	
		BDX34C		
		BDX33	45	
		BDX34		



C O M S E T
S E M I
C O N D U C T O R S

**NPN BDX33 – BDX33A – BDX33B – BDX33C
PNP BDX34 – BDX34A – BDX34B – BDX34C**

Symbol	Ratings		Value	Unit	
I_C	Collector Current	$I_{C(RMS)}$	10	A	
			BDX33		
			BDX33A		
			BDX33B		
			BDX33C		
		I_{CM}	15		
			BDX34		
			BDX34A		
			BDX34B		
			BDX34C		
I_B	Base Current	@ $T_C = 25^\circ$	0.25	A	
			BDX33		
			BDX33A		
			BDX33B		
			BDX33C		
			BDX34		
			BDX34A		
P_T	Power Dissipation	@ $T_C = 25^\circ$	70	Watts W/ $^\circ$ C	
			BDX33		
			BDX33A		
			BDX33B		
			BDX33C		
			BDX34		
			BDX34A		
T_J	Junction Temperature		-65 to +150	$^\circ$ C	
			BDX34B		
T_S	Storage Temperature		BDX34C		
			BDX34C		



C O M S E T
S E M I
C O N D U C T O R S

**NPN BDX33 – BDX33A – BDX33B – BDX33C
PNP BDX34 – BDX34A – BDX34B – BDX34C**

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	1.78	°C/W

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=100\text{ mA}$	BDX33 BDX34	45	-	-	
			BDX33A BDX34A	60	-	-	V
			BDX33B BDX34B	80	-	-	
			BDX33C BDX34C	100	-	-	
$V_{CER(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_B=100\text{ mA}, R_{BE}=100\Omega$	BDX33 BDX34	45	-	-	
			BDX33A BDX34A	60	-	-	V
			BDX33B BDX34B	80	-	-	
			BDX33C BDX34C	100	-	-	



C O M S E T
S E M I
C O N D U C T O R S

**NPN BDX33 – BDX33A – BDX33B – BDX33C
PNP BDX34 – BDX34A – BDX34B – BDX34C**

Symbol	Ratings	Test Condition(s)		Min	Typ	Mx	Unit
$V_{CEV(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_C=100\text{ mA}$, $V_{BE}=-1.5\text{ V}$	BDX33	45	-	-	V
			BDX34				
			BDX33A	60	-	-	
			BDX34A				
I_{CEO}	Collector Cutoff Current	$T_{CASE}=25^\circ\text{C}$	BDX33				mA
			BDX34	-	-		
			BDX33A				
			BDX34A	-	-		
		$T_{CASE}=100^\circ\text{C}$	BDX33				
			BDX34	-	-		
			BDX33A				
			BDX34A	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE}=-5\text{ V}$	BDX33				mA
			BDX33A				
			BDX33B				
			BDX33C				
			BDX34				
			BDX34A				
			BDX34B				
			BDX34C				
I_{CBO}	Collector-Base Cutoff Current	$T_{CASE}=25^\circ\text{C}$	BDX33				mA
			BDX34	-	-		
			BDX33A				
			BDX34A	-	-		



C O M S E T
S E M I
C O N D U C T O R S

**NPN BDX33 – BDX33A – BDX33B – BDX33C
PNP BDX34 – BDX34A – BDX34B – BDX34C**

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
I_{CBO}	Collector-Base Cutoff Current	$V_{CBO}=45\text{ V}$	BDX33	-	-	mA
		$V_{CBO}=60\text{ V}$	BDX34	-	-	
		$V_{CBO}=80\text{ V}$	BDX33A	-	-	
		$V_{CBO}=100\text{ V}$	BDX34A	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=4.0\text{ A}, I_B=8.0\text{ mA}$	BDX33	-	-	2.5
		$I_C=4.0\text{ A}, I_B=8.0\text{ mA}$	BDX33A	-	-	
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX34	-	-	
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX34A	-	-	
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX33B	-	-	2.5
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX33C	-	-	
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX34B	-	-	
		$I_C=3.0\text{ A}, I_B=6.0\text{ mA}$	BDX34C	-	-	
V_F	Forward Voltage (pulse method)	$I_F=8\text{ A}$	BDX33	-	-	4.0
			BDX33A	-	-	
			BDX33B	-	-	
			BDX33C	-	-	
			BDX34	-	-	
			BDX34A	-	-	
			BDX34B	-	-	
V_{BE}	Base-Emitter Voltage (*)	$I_C=4.0\text{ A}, V_{CE}=3.0\text{V}$	BDX33	-	-	2.5
			BDX33A	-	-	
			BDX34	-	-	
			BDX34A	-	-	
		$I_C=3.0\text{ A}, V_{CE}=3.0\text{V}$	BDX33B	-	-	2.5
			BDX33C	-	-	
			BDX34B	-	-	
			BDX34C	-	-	
h_{FE}	DC Current Gain (*)	$V_{CE}=3.0\text{ V}, I_C=4.0\text{ A}$	BDX33	750	-	-
			BDX33A		-	
			BDX34		-	
			BDX34A		-	
		$V_{CE}=3.0\text{ V}, I_C=3.0\text{ A}$	BDX33B	750	-	-
			BDX33C		-	
			BDX34B		-	
			BDX34C		-	

(*) Pulse Width $\approx 300\text{ }\mu\text{s}$, Duty Cycle $\angle 2.0\%$

(1) collector-Emitter voltage limited et $V_{CEci} = V_{\text{rated}}$ by an auxiliary circuit

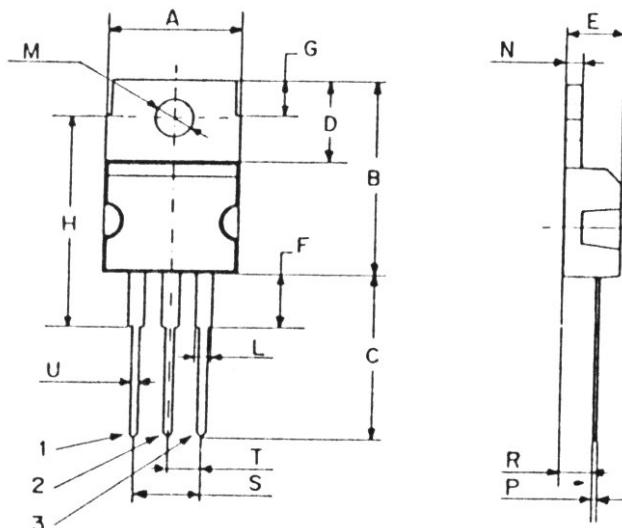


COMSET
SEMICONDUCTORS

**NPN BDX33 – BDX33A – BDX33B – BDX33C
PNP BDX34 – BDX34A – BDX34B – BDX34C**

MECHANICAL DATA CASE TO-220

DIMENSIONS		
	mm	inches
A	9,86	0,39
B	15,73	0,62
C	13,37	0,52
D	6,67	0,26
E	4,44	0,17
F	4,21	0,16
G	2,99	0,11
H	17,21	0,68
L	1,29	0,05
M	3,6	0,14
N	1,36	0,05
P	0,46	0,02
R	2,1	0,08
S	5	0,19
T	2,52	0,098
U	0,79	0,03



Pin 1 :	base
Pin 2 :	Collector
Pin 3 :	emitter